

Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1. (Currently Amended) A method comprising:  
forming a first electrode and a second electrode on a base body; and  
chemically etching at least a portion of the base body, the first electrode, and the second electrode with an etching solution ~~comprising an acid~~ to adjust a resistance of the base body between the first electrode and the second electrode[.];  
wherein the first and second electrodes are made from a material that is ~~not etchable by the etching solution or that is~~ etchable, by the etching solution, substantially less than the base body is etchable by the etching solution.
2. (Original) The method of claim 1, wherein the base body comprises a ceramic material.
3. (Original) The method of claim 1, wherein the base body comprises a material having a resistance with a negative temperature coefficient.
4. (Original) The method of claim 1, wherein a length of an edge of the base body is less than about 3 mm.

5. (Currently Amended) The method of claim 1, wherein chemically etching at least a portion of the base body, the first electrode, and the second electrode comprises immersing the base body, the first electrode, and the second electrode in [[an]] the etching solution liquid.

6. (Currently Amended) The method of claim 1, wherein the [[acid]] etching solution is sulfuric acid.

7. (Original) The method of claim 1, further comprising measuring a value of a resistance of the base body prior to chemically etching the at least a portion of the base body.

8. (Canceled)

9. (Original) The method of claim 1, further comprising:  
determining a difference between the predetermined value and a measured value of the resistance; and

determining a duration for the chemically etching based on said difference, wherein chemically etching at least a portion of the base body comprises chemically etching at least a portion of the base body for the duration.

10. (Original) The method of claim 1, wherein forming the first electrode and the second electrode on the base body comprises forming the first electrode at a location opposite the second electrode on the base body.

11. (Original) The method of claim 1, wherein chemically etching at least a portion of the base body to adjust the resistance of the base body comprises chemically etching at least a portion of the base body to adjust the resistance of the base body to a predetermined value.

12. (Previously Presented) The method of claim 1, wherein the first and second electrodes comprise a multilayer metallization comprising a Ag/Ni/Sn layer sequence.

13. (Previously Presented) The method of claim 1, wherein the first and second electrodes comprise a silver/palladium metallization.

14. (Currently Amended) A method comprising:  
forming a first electrode and a second electrode on a base body; and  
chemically etching at least a portion of the base body, the first electrode, and the second electrode with an etching solution to adjust a resistance of the base body between the first electrode and the second electrode, wherein the first and second electrodes comprise a multilayer metallization comprising a Ag/Ni/Sn layer sequence.

15. (Currently Amended) A method comprising:  
forming a first electrode and a second electrode on a base body; and  
chemically etching at least a portion of the base body, the first electrode, and the second  
electrode with an etching solution to adjust a resistance of the base body between the first  
electrode and the second electrode, wherein the first and second electrodes comprise a  
silver/palladium metallization.